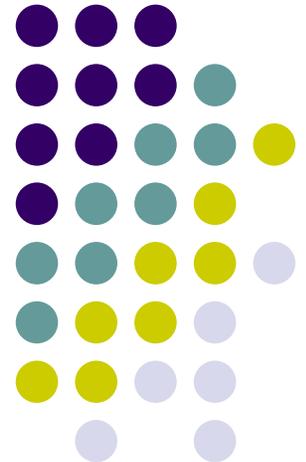
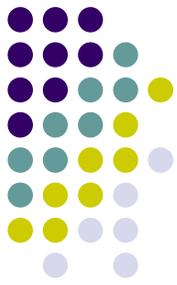


Fine Pixel CCD Option for the ILC Vertex Detector

19 Mar. 2005
@LCWS2005
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KEK





Vertex Detector Options

- If the hit signal is accumulated for one train of 2820 bunches, too many hits by beam b.g. → for 25 μm pixels, the pixel occupancy $> 20\%$
- Solutions;
 - Fast readout : Column Parallel CCD @50MHz, 20 frames/train
 - Possible effect by RF noise by beam
 - Analog registers in each pixel ($\sim 20/\text{pixel}$), and readout between trains
 - CMOS: Flexible Active Pixel Sensor (FAPS)
 - CCD: In-situ Storage Image Sensor (ISIS)
 - Complicated structure → Large area OK?
 - Make pixel density x20 → **Fine Pixel CCD (FPCCD)**

Vertex Detector Options

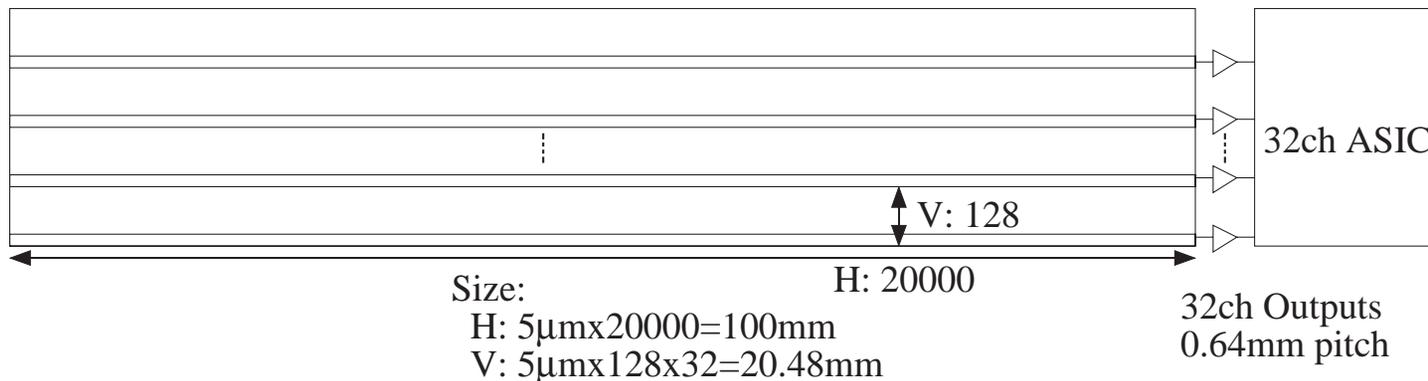
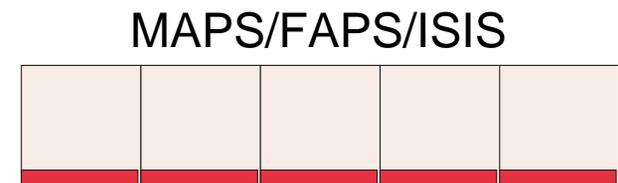
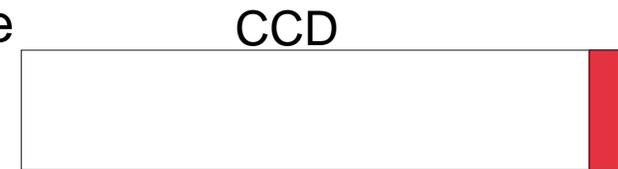


- FPCCD
 - Accumulate hit signals for one train and read out between trains
 - Keep low pixel occupancy by increasing number of pixels by x20 with respect to “standard” pixel detector
 - As a result, pixel size should be as small as $\sim 5 \times 5 \mu\text{m}^2$
 - Epitaxial layer has to be fully depleted to minimize charge spread by diffusion
 - Operation at low temperature to keep dark current negligible (r.o. cycle=200ms)



Advantages of FPCCD

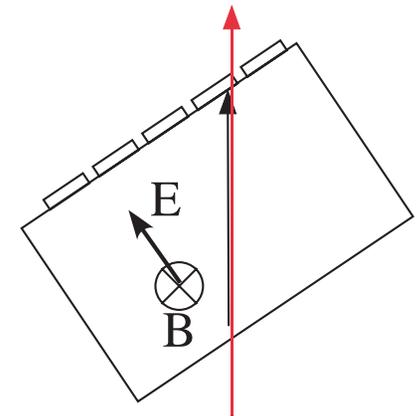
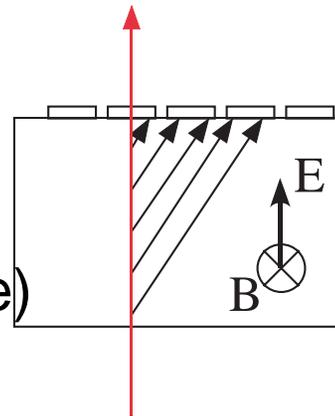
- Free from beam-induced RF noise
- $\sigma_x \sim 1.4\mu\text{m}$ even with digital readout
- Simple structure : advantageous for large size
- Active circuit on one edge : easy to control temperature
- Readout speed: 15MHz is enough
($128(V) \times 20000(H) / 200\text{ms} = 12.8\text{MHz}$)
(CPCCD: $>50\text{MHz}$)





Challenges of FPCCD

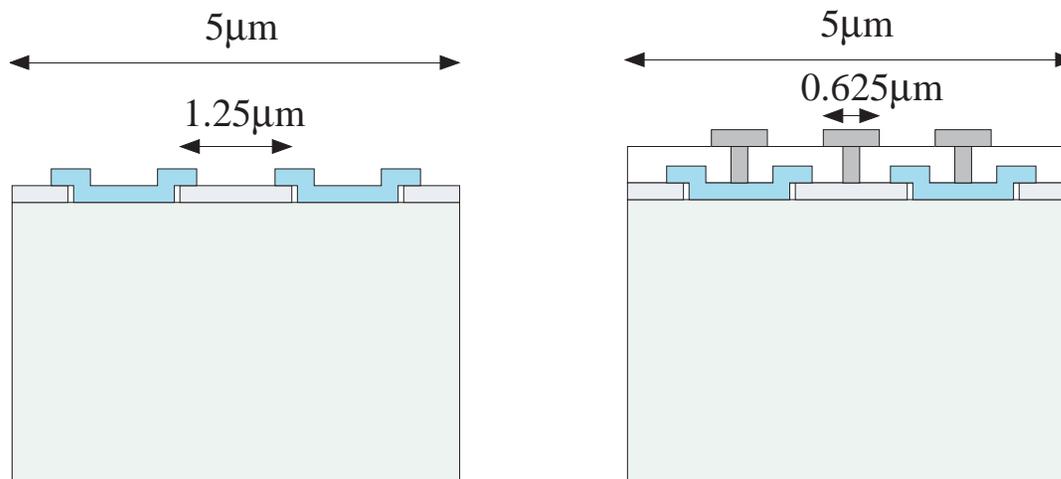
- Pixel size
- Horizontal register in image area
- Tracking efficiency
- Thin wafer and support structure
 - 50 μm thick, 20x100mm²
- Lorentz angle
 - Low B is preferable
- Readout electronics
 - Signal level is small (~ 500 e)
- Radiation hardness
 - Relaxed by low temp. operation





Pixel Size

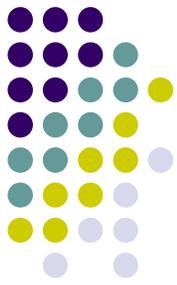
- $5\mu\text{m}$ pixel of fully depleted CCD has full-well capacity of only few k electrons
- CCD process
 - $5\mu\text{m}$ pixel with poly-Si gate is easy ($1.6\mu\text{m}$ pixel CCD for cameras on mobile phone already exists)
 - Large size and fast readout require Al layer
 - Large size CCD with $5\mu\text{m}$ pixel with poly-Si gate and metal layer is not easy



Tracking Efficiency

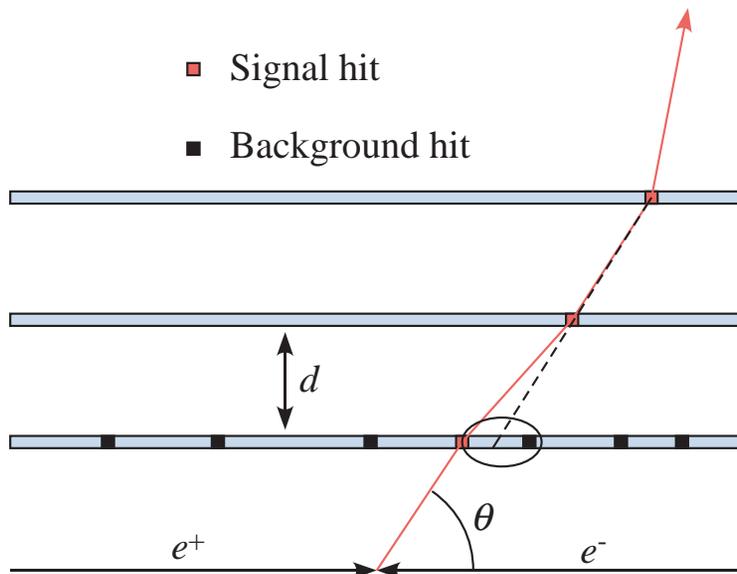


- In FPCCD, pixel occupancy would be low ($\sim 1\%$) but hit density mainly due to the pair-background is as high as $\sim 40/\text{mm}^2$ ($B=3\text{T}$, $R=20\text{mm}$, $L=3.4 \times 10^{34}$)
- So, it is not trivial whether we can get good tracking efficiency
- Extrapolation of tracks from Si intermediate tracker (SIT) with bunch ID capability will be necessary
- The study of tracking efficiency under high background rate is the most important and urgent issue
- Simulation framework to overlap background hits with physics events has to be constructed



Tracking Efficiency

- Large number of background hits may cause tracking inefficiency: mis-identification of signal hit with background hit



For a normal incident track, the probability of mis-identification of hit is given by;

$$p_{mis} = 2\pi\sigma R_0^2, R_0 = d\theta_0$$

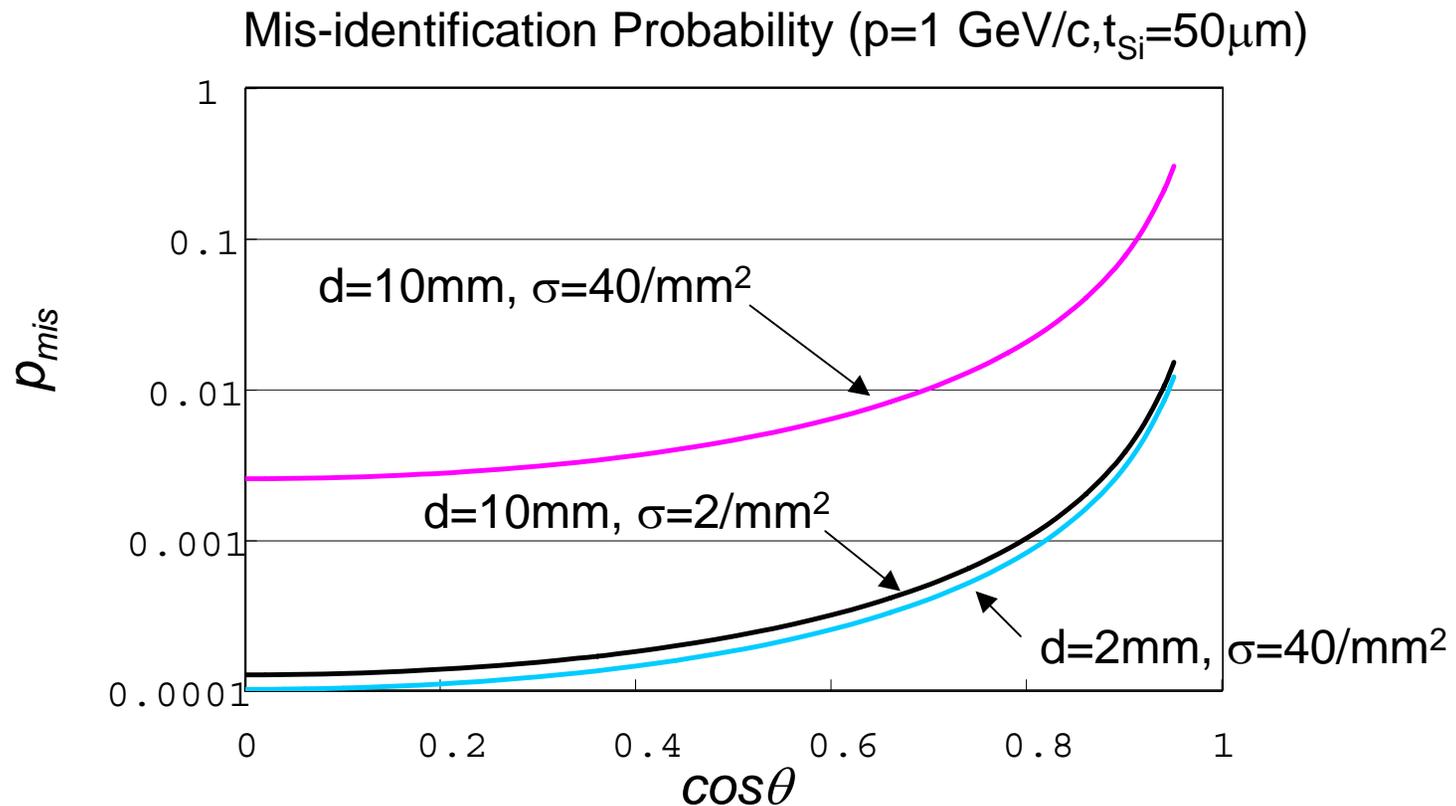
σ : Background hit density

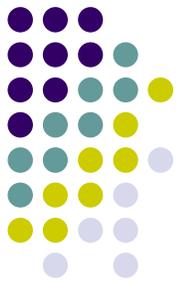
θ_0 : Multiple scattering angle

Angular and momentum dependence;

$$p_{mis} \propto p^{-2} \sin^{-4} \theta$$

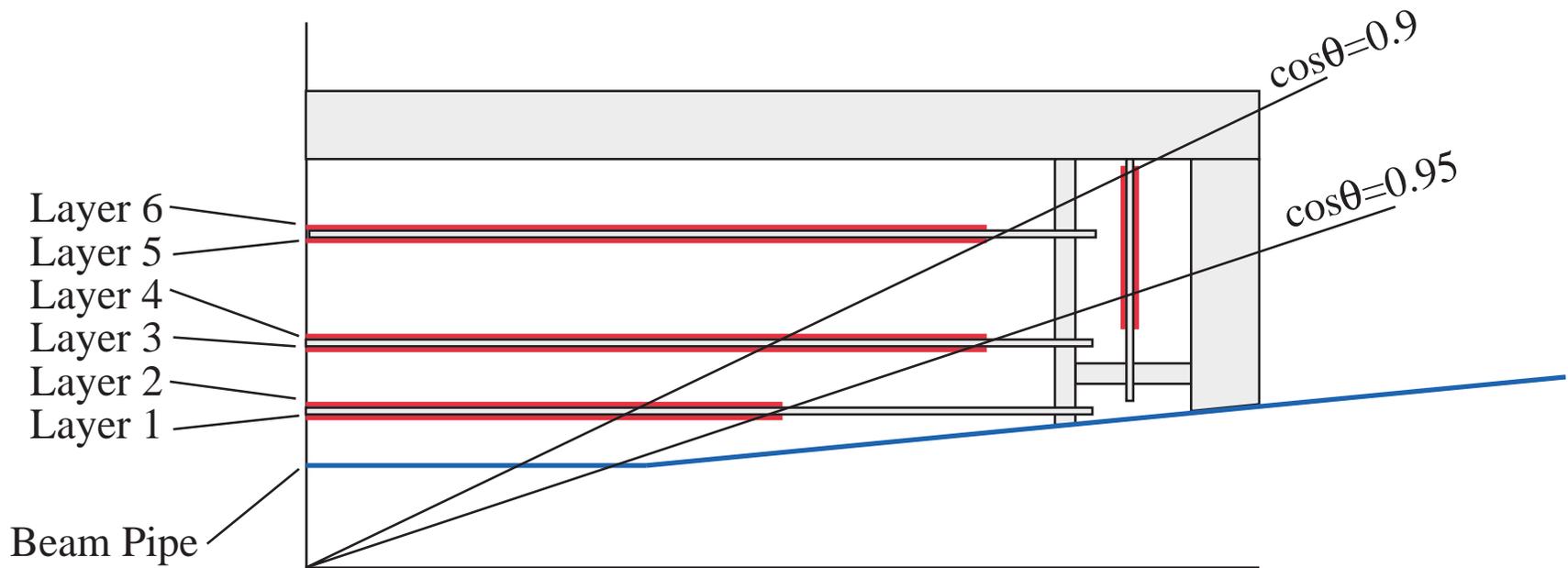
Tracking efficiency





Tracking Efficiency

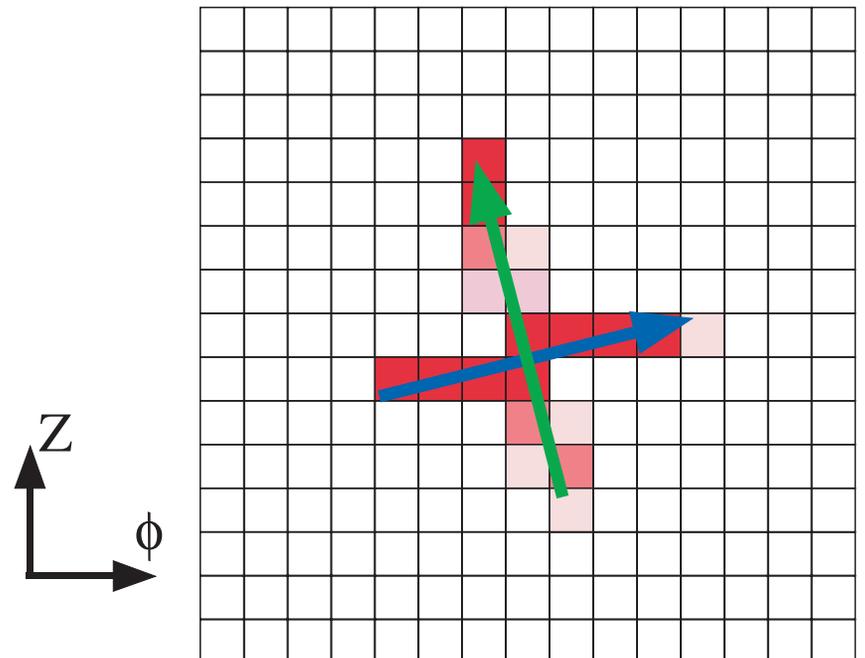
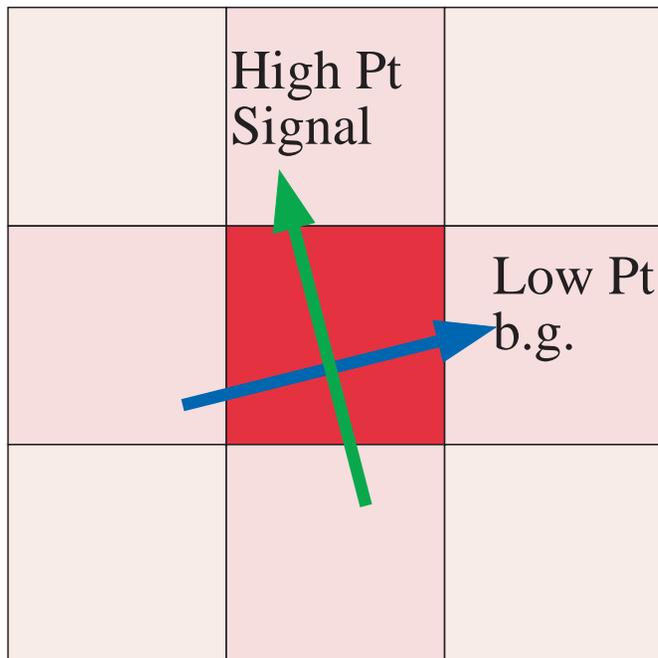
- Some ideas for b.g. rejection (1)
 - CCD doublet in proximity to reduce effect of M.S.





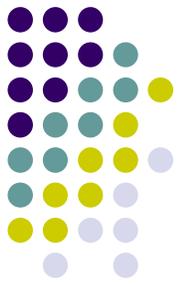
Tracking Efficiency

- Some ideas for b.g. rejection (2)
 - Hit cluster shape

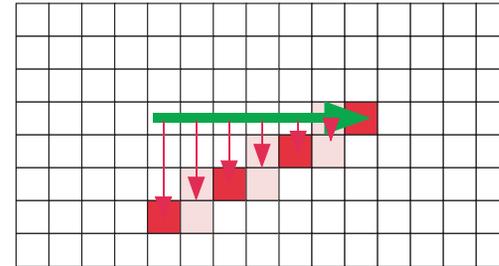


(tracking capability with single layer!)

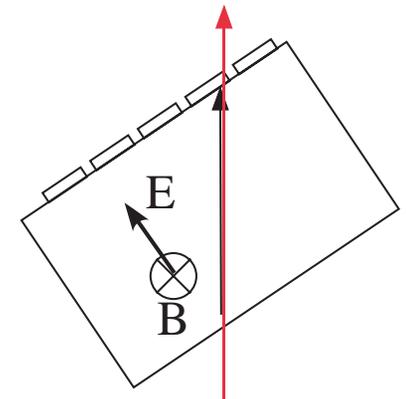
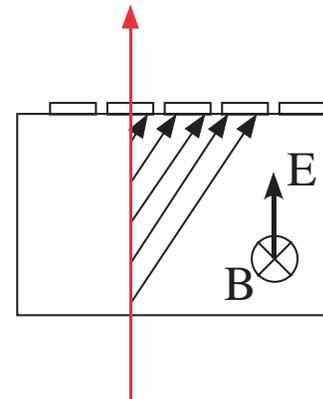
Lorentz Angle



- Lorentz angle in depleted-layer
 - $\tan\theta = \mu_n B$
 μ_n : electron mobility
 - Carrier velocity saturates at high E field:
 - $\mu_n = 0.07 \text{ m}^2/\text{Vs}$
 @ $T=300\text{K}$, $E=1 \times 10^4 \text{ V/cm}$
 - $\mu_n = 0.045 \text{ m}^2/\text{Vs}$
 @ $T=300\text{K}$, $E=2 \times 10^4 \text{ V/cm}$
 - Small angle can be cancelled by tilting the wafer
- May not be a serious problem
 - Number of hit pixels does not increase so much



	B=3T	B=5T
$E=1 \times 10^4 \text{ V/cm}$	$\theta=12\text{deg}$	$\theta=19\text{deg}$
$E=2 \times 10^4 \text{ V/cm}$	$\theta=7.7\text{deg}$	$\theta=13\text{deg}$





Study Issues of FPCCD

- Short term goal (by the “Detector outline document”)
 - Simulation study
 - Tracking efficiency
 - Physics implication (Flavor tagging)
 - Hardware study (depends on funding)
 - Charge spread in fully depleted CCDs
 - Lorentz angle in B field → Optimization of wafer tilt angle
 - Radiation hardness (difference in fully depleted CCD?)
 - Show that FPCCD works as a vertex detector “in principle”
- Mid term goal (by “CDR”)
 - Fabrication of prototype ladders
 - Test the prototypes and demonstrate the performance
- Long term goal (by “LOI”)
 - Engineering design of FPCCD Vertex Detector

Summary



- We propose FPCCD option for the ILC Vertex Detector
 - Fully depleted CCD with $5\mu\text{m}$ -square fine pixel size
 - Accumulate 2820 BX and readout between trains
 - Two layers make a doublet (super layer) to pick up signal hits out of background hits
- FPCCD seems the most feasible (least challenging) technology among the proposed options
- Tracking efficiency under beam background is the most critical issue for FPCCD. Simulation study is urgent.